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ACKNOWLEDGEMENTS

With the immense blessing of *Baba Vishwanath and Maa Sharde*, I was able to complete my thesis. I would like to express my immense gratitude to my supervisor Prof. P. K. Jain and Dr. Smrity Dwivedi for their excellent guidance and motivation. The completion of this research work is truly an outcome of his constant untiring support, valuable ideas, and suggestions during my research work. The insightful discussions with him always provided me great enthusiasm.

I would like to express my special thanks to Arjun Kumar for his valuable technical discussion and all my dear colleagues for creating the friendly and happy environment needed for completing my work. My thanks and deep appreciations also go to all staff members of CRMT, especially to Mr. Rajesh Kumar Rai for their kind co-operation.

I would like to express my deep appreciation to my colleague and roommate Deepak Jarwal and Amit Kumar who helped me in every phase of the PhD. I wish to express indebtedness to Sudhakar Tripathi, Shasikant Tiwari, Jitendra Kumar, Deepak Rathore, Satyavrat Tripathi, Kunwar Vishwanath Pratap Singh, Singh Divakar Virendra Kumar, Awadesh Kumar Maurya, Raj Kumar Arya, and Rahul Ranjan for their unconditional love, extreme patience, and constant support over the years. They provide me the strength and confidence to attain this task.

My deepest appreciation towards my Parents and my wife Arti Tiwari for her continuous support and patience. They always being a source of strength for me and remain an invaluable asset to me. I have a deep appreciation for my family for providing enormous moral support.

Finally, I hearty express sincere thanks to the Ministry of Electronics and Information Technology, Government of India for providing me financial support through the Visvesvaraya PhD Scheme.

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Dedicated
To
My Parents

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ABBREVIATIONS

Abbreviation	Details
3D	Three Dimensional
A	Ampere
A-K	Anode-Cathode
DC	Direct Current
DEW	Directed Energy Weapon
EM	Electromagnetic
EMP	Electromagnetic Pulse
FEL	Free Electron Laser
GHz	GigaHertz
HPM	High Power Microwave
Hz	Hertz
IREB	Intense Relativistic Electron Beam
J	Joules
kJ	Kilo Joule
kA	Kilo Ampere
kV	Kilo Volt
LINAC	Linear Accelerator
MA	Mega Ampere

MHz	Mega Hertz
MILO	Magnetically Insulated Line Oscillator
mm	Millimeter
MW	Megawatt
NM	New Mexico
ns	Nanosecond
PIC	Particle-In-Cell
BWO	Backward Wave Oscillator
RBWO	Relativistic Backward Wave Oscillator
RKO	Relativistic Klystron Oscillator
RTTO	Relativistic Transit Time Oscillator
RF	Radio Frequency
SCO	Split Cavity Oscillator
SWS	Slow Wave Structure
TE	Transverse Electric
TM	Transverse Magnetic
VIRCATOR	Virtual Cathode Oscillator

LIST OF SYMBOLS

Symbol	Details
R_0	Equivalent Resistance
L_0	Equivalent Inductance
C_0	Equivalent Capacitance
$[I]$	Current vector
$[0]$	Zero vector
$[A]$	Matrix vector
ω_{res}	Fundamental resonating frequency of the equivalent circuit
ϵ_0	Free space permittivity
I_0	Total RF current flows inside the main cavity of the SCC
β_0	Fundamental axial propagation constant of the RF wave
k	Coupling factor
r_c	Cathode radius
r	Radius
r_e	Electron beam radius
r_{mc}	Main cavity radius
r_h	Coupled cavity radius
r_{cc}	Disc hole radius
L	Periodicity of the SCC
E_r	Radial electric field intensity
E_θ	Azimuthal electric field intensity
E_z	Axial electric field intensity
B_r	Radial magnetic field intensity
B_θ	Azimuthal magnetic field intensity
P_z	Axial momentum
γ	Relativistic factor
J_z	Axial current density

n_e	charge number density
v_z	axial drift velocity
c	Speed of light
e	Charge of the electron
m_e	Mass of the electron
k_c	Free space propagation constant
I_e	Beam current
V_e	Beam voltage
$J(\Gamma r)$	Bessel function
Γ	Radial propagation constant of the RF wave
v_e	Electron velocity by $\omega = \beta_0 v_e$) and slow space charge wave (slow
v_{slow_sc}	The velocity of slow space charge wave
f_i	Imaginary resonating frequency
f_r	Resonating frequency/ Real frequency
(r, θ, z)	Cylindrical-coordinate system
χ_m	Eigenvalue of the cylindrical waveguiding system
V_{tube}	Total tube voltage
r_{id}	Idler radius
λ_e	Wavelength of the velocity of an electron
d_{opt}	Optimal disk spacing
d_{AK}	Anode-cathode gap
L_{PA}	Length of post-acceleration region
L_{ext}	Length of the extraction cavity
k_z	Wavenumber
L_{dt}	Length of the drift tube
B_z^*	External magnetic field